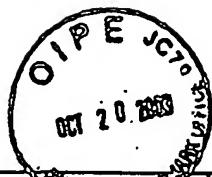


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Sheet 1 of 1

FORM PTO-1449 US Dept. of Commerce Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)			ATTORNEY DOCKET NO.		SERIAL NO.		
			ATMI-661		10/618,024		
			APPLICANT		Robert P. Vaudo, et al.		
			FILING DATE		GROUP		
July 11, 2003		TBA					
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING /PUBLICATION DATE IF APPROPRIATE
<i>SC</i>	AA	6,273,948 B1	8/14/2001	Porowski, et al.	—	—	
<i>SC</i>	AB	5,385,862	1/31/1995	Moustakas	—	—	
<i>SC</i>	AC	6,544,867 B1	4/8/2003	Webb, et al.	—	—	
<i>SC</i>	AD	5,686,738	11/7/1997	Moustakas	—	—	
<i>SC</i>	AE	6,261,931 B1	7/17/2001	Keller, et al.	—	—	
<i>SC</i>	AF	US 2002/0096692 A1	7/26/2002	NAKAMURA et al.	257	194	7/25/2002
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLAS S	TRANSLATION YES NO
							X (abstract only)
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<i>SC</i>	AG	Jerzy M. Langer, et al. "Transition-metal impurities in semiconductor and heterojunction band lineups", Physical Review B, Vol. 38, No. 11, pgs. 7723-7739, 15 Oct. 1988.					
<i>SC</i>	AH	T. Graf, et al., "The Mn ^{3+/-} acceptor level in group III nitrides", Applied Physics Letters, Vol. 81, No. 27, pgs. 5159-5161, 30 Dec. 2002.					
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EXAMINER	<i>Miller</i>			DATE CONSIDERED <i>7/18/04</i>			
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INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)		APPLICANT Robert P. Vaudo, et al.	
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AN	R. Heitz, et al., "Zeeman spectroscopy of the Fe ³⁺ center in GaN", Appl. Phys. Lett. 67 (19), pgs. 2822-2824, 6 Nov. 1995.
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EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING/ PUBLICATION DATE IF APPROPRIATE
	BA	5,679,152	10/21/1997	Tischler, et al.	—	—	
	BB	6,156,581	12/5/2000	Vaudo, et al.	—	—	
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